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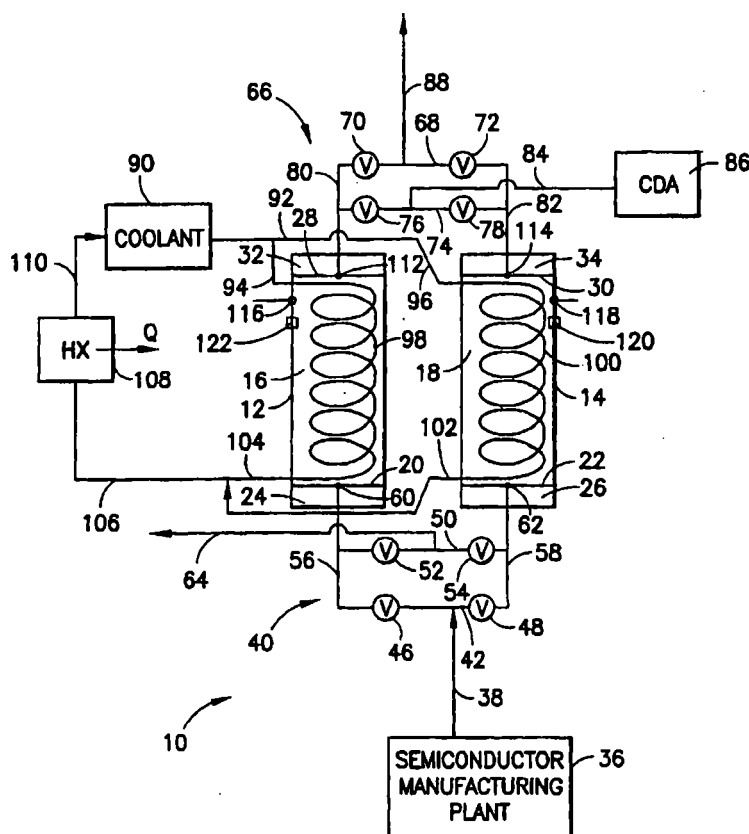
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(54) Title: IN-SITU AIR OXIDATION TREATMENT OF MOCVD PROCESS EFFLUENT



(57) Abstract: Effluent abating system (10) for abating hydride species in a hydride-containing effluent, arranged for carrying out the steps of: contacting the hydride-containing effluent with a dry scrubber material comprising a metal oxide that is reactive with hydride species to remove the hydride species from the effluent, until the capacity of the dry scrubber material for hydride species is at least partially exhausted; and contacting the at least partially exhausted capacity dry scrubber material with an oxidant to at least partially regain the capacity of the dry scrubber material for the hydride species. The system of the invention has particular utility in the treatment of effluent from III-V compound semiconductor manufacturing operations from the manufacturing plant (36).



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\*ACTION\*

WO 01/37985 A1

## WO 01/37985 A1

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